

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	69	(438/722).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 14:31
2	BRS	69	((("438/722").CCLS.) and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 13:26
3	BRS	223162	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 16:06
4	BRS	35716	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:15
5	BRS	4864	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:12
6	BRS	1	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet') and 'group IV metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:14
7	BRS	16571	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:21
8	BRS	61	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:25
9	BRS	104	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:25
10	BRS	36	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'amorphous oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:26
11	BRS	1	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum' and 'amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/14 14:26
12	BRS	224025	438/\$.ccls. or 257/\$.ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 11:50
13	BRS	15	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 10:49
14	BRS	4906	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 10:51
15	BRS	73	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 15:23
16	BRS	24	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium') and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/15 10:55
17	IS&R	2	("6020024").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 11:22
18	IS&R	4	("4432035").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 13:44
19	IS&R	417	(257/411).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 16:09
20	BRS	5	((("257/411").CCLS.) and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 13:46
21	BRS	230368	438/\$.ccls. or 257/\$.ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 11:54
22	BRS	168	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 13:13
23	BRS	2	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'hafnium' and 'combining' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 12:02
24	BRS	91	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'hafnium' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 12:07
25	BRS	67	'hafnium' with 'reaction' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 12:32
26	BRS	3	'hafnium oxide' near 'formation'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 12:33
27	BRS	58	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'silicon oxide' and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 15:42
28	BRS	51	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'metal' with 'reduces' with 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 13:42

	Type	Hits	Search Text	DBs	Time Stamp
29	BRS	199	(438/785).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 14:02
30	BRS	51	((438/785).ccls. and @ad<=20010613) and 'Hf'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 14:05
31	BRS	32	((438/785).ccls. and @ad<=20010613) and 'Hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 14:06
32	IS&R	4	("4432035").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 14:32
33	BRS	1	"2693629".PN.	USPAT	2002/06/25 14:35
34	BRS	1	"3819990".PN.	USPAT	2002/06/25 14:35
35	BRS	1	"4062749".PN.	USPAT	2002/06/25 14:38
36	BRS	1	"4227944".PN.	USPAT	2002/06/25 14:38
37	BRS	1	"5106827".PN.	USPAT	2002/06/25 15:21
38	BRS	1	"5106827".PN.	USPAT	2002/06/25 15:21
39	BRS	1	"5187638".PN.	USPAT	2002/06/25 15:21
40	BRS	1	"5188902".PN.	USPAT	2002/06/25 15:21
41	BRS	1	"5273927".PN.	USPAT	2002/06/25 15:22
42	BRS	1	"6177361".PN.	USPAT	2002/06/25 15:22
43	BRS	1	"5824590".PN.	USPAT	2002/06/25 15:22
44	BRS	1	"5773314".PN.	USPAT	2002/06/25 15:22
45	BRS	1	"5572052".PN.	USPAT	2002/06/25 15:22
46	BRS	90	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/25 16:05
47	BRS	0	@ad<=20010613 and 'reduces' with 'silicon dioxide to silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 15:44
48	BRS	1028	@ad<=20010613 and 'reduces' with 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 15:47
49	BRS	29	@ad<=20010613 and 'reduces' adj 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 16:01
50	BRS	4	@ad<=20010613 and 'hafnium' adj 'silicon dioxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 15:55
51	BRS	1	@ad<=20010613 and 'hafnium' adj 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 15:55
52	BRS	126214	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113 and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 16:09
53	BRS	124737	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113 and 'high dielectric' and 'silicon oxide' and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 08:52
54	BRS	31	@ad<=20010113 and 'PVD' with 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 11:45
55	BRS	393	@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:01
56	BRS	393	@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombardment energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 09:04
57	BRS	13419	@ad<=20010113 and 'high dielectric constant'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 09:08
58	BRS	332	(@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 09:09

Type	Hits	Search Text	DBs	Time Stamp
59	BRS 0	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:10
60	BRS 16	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:10
61	BRS 1	"4495219".PN.	USPAT	2002/07/11 10:00
62	BRS 1	"6013553".PN.	USPAT	2002/07/11 10:00
63	BRS 1	"6015739".PN.	USPAT	2002/07/11 10:00
64	BRS 1	"5464792".PN.	USPAT	2002/07/11 10:00
65	BRS 1	"6020024".PN.	USPAT	2002/07/11 10:01
66	BRS 1	"6020243".PN.	USPAT	2002/07/11 10:01
67	BRS 1	"6060755".PN.	USPAT	2002/07/11 10:01
68	BRS 1	"6110784".PN.	USPAT	2002/07/11 10:01
69	BRS 6	@ad<=20010113 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 11:46
70	BRS 22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 11:52
71	BRS 3	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 11:51
72	BRS 3	@ad<=20010113 and 'hafnium' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 13:13
73	BRS 53	@ad<=20010113 and 'metal' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 12:56
74	BRS 0	@ad<=20010113 and 'refractory metal' with 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:13
75	BRS 1	"4520413".PN.	USPAT	2002/07/11 13:08
76	BRS 1	"5930611".PN.	USPAT	2002/07/11 13:08
77	BRS 1	"6054331".PN.	USPAT	2002/07/11 13:09
78	BRS 1	"6060391".PN.	USPAT	2002/07/11 13:11
79	BRS 1	"6069070".PN.	USPAT	2002/07/11 13:12
80	BRS 266	@ad<=20010113 and 'hafnium' with 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 13:15
81	BRS 22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:01
82	BRS 22	@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:09
83	BRS 1	"4173661".PN.	USPAT	2002/07/23 12:08
84	BRS 1	"5773363".PN.	USPAT	2002/07/23 12:08
85	BRS 5	@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment' with 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:16
86	BRS 6	@ad<=20010613 and 'PVD' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:40
87	BRS 3	@ad<=20010613 and 'hafnium' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:52
88	BRS 29	@ad<=20010613 and 'PVD' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:38
89	BRS 67	@ad<=20010613 and 'sputter' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:39
90	BRS 19	@ad<=20010613 and 'hafnium' and 'sputter' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:50

	Type	Hits	Search Text	DBs	Time Stamp
91	BRS	4	@ad<=20010613 and 'hafnium' and 'sputter' and 'oxygen radical' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:44
92	BRS	0	@ad<=20010613 and 'hafnium' and 'I-PVD' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:50
93	BRS	6	@ad<=20010613 and 'hafnium' and 'Ionized' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:50
94	BRS	14	@ad<=20010613 and 'hafnium' and 'ion bombardment' and 'sputter' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:01
95	BRS	912	@ad<=20010613 and 'dielectric deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:10
96	BRS	118	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal')	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:09
97	BRS	0	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'sputter' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 13:07
98	BRS	1	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'sputter' and	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:09
99	BRS	0	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'PVD' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:09
100	BRS	12	((@ad<=20010613 and 'dielectric deposition') and 'hafnium')	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:09
101	BRS	0	@ad<=20010613 and 'hafnium deposition' and 'PVD' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:14
102	BRS	0	@ad<=20010613 and 'hafnium deposition' and 'sputter' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:15
103	BRS	6	@ad<=20010613 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:15
104	BRS	96	@ad<=20010613 and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:19
105	BRS	3	((@ad<=20010613 and 'ion bombardment' with 'eV') and 'hafnium')	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 13:20
106	IS&R	2	("6399521").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 14:33